

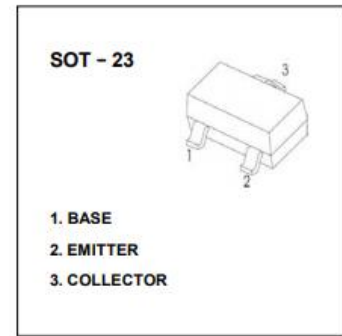


## SOT-23 Plastic-Encapsulate Transistors

**SS8550** TRANSISTOR (PNP)

### FEATURES

Complimentary to SS8050 0.7A



### MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol (符号)	Parameter (参数名称)	Value (额定值)	Units (单位)
VCBO	Collector-Base Voltage (集电极-基极电压)	-40	V
VCEO	Collector-Emitter Voltage (集电极-发射极电压)	-25	V
VEBO	Emitter-Base Voltage (发射极-基极电压)	-5	V
IC	Collector Current -Continuous (集电极电流)	-0.7	A
PC	Collector Power Dissipation (耗散功率)	-0.3	W
Tj	Junction Temperature (结温)	150	°C
Tstg	Storage Temperature (储存温度)	-55-150	°C

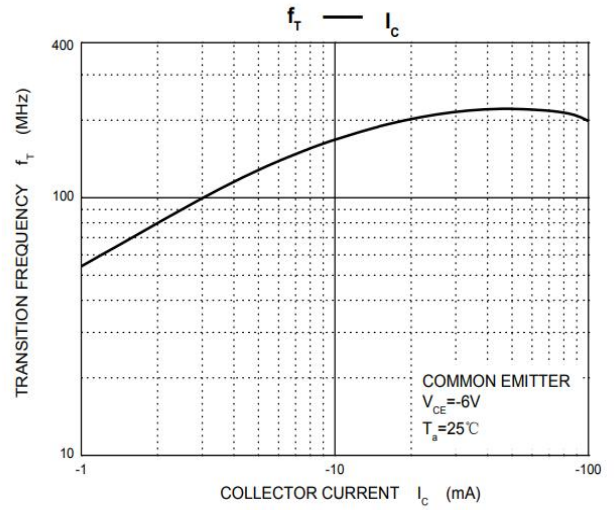
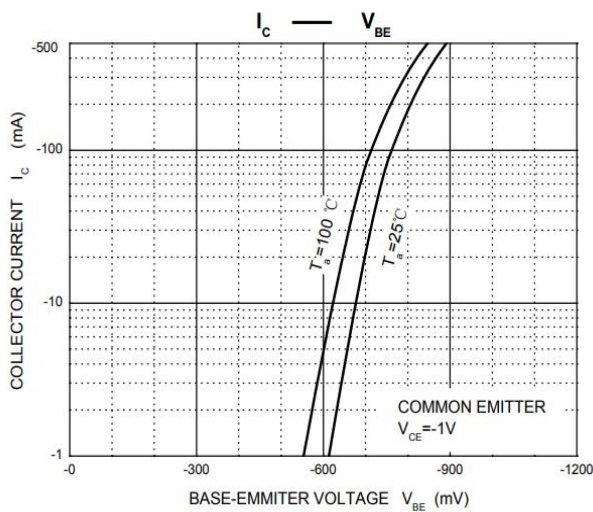
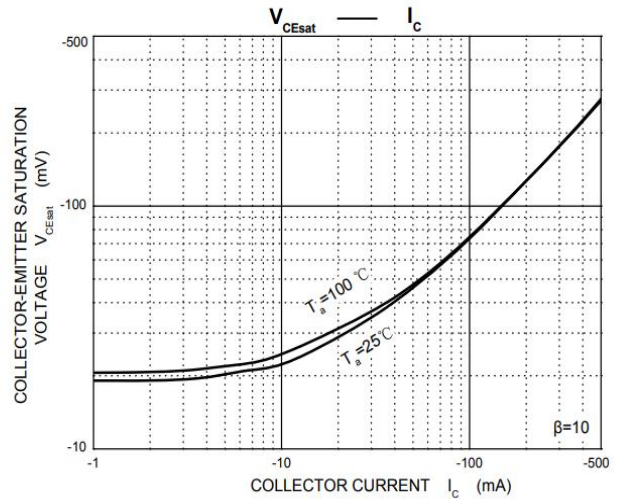
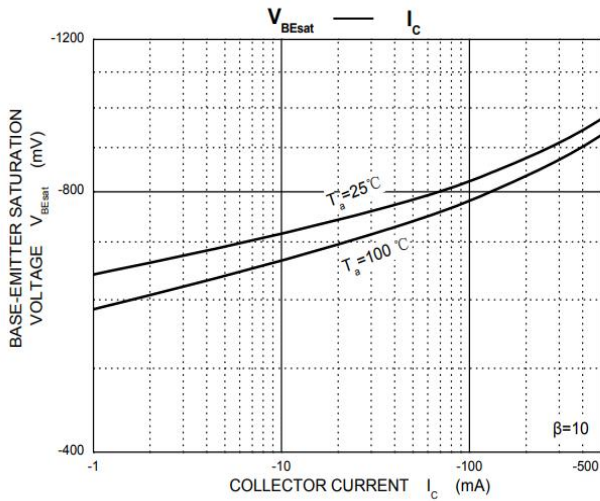
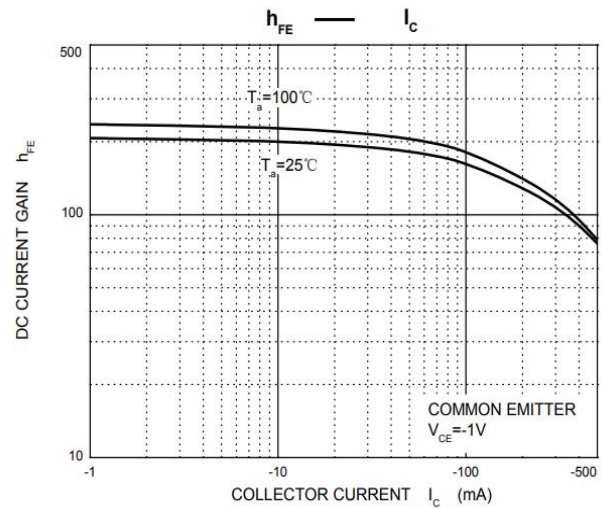
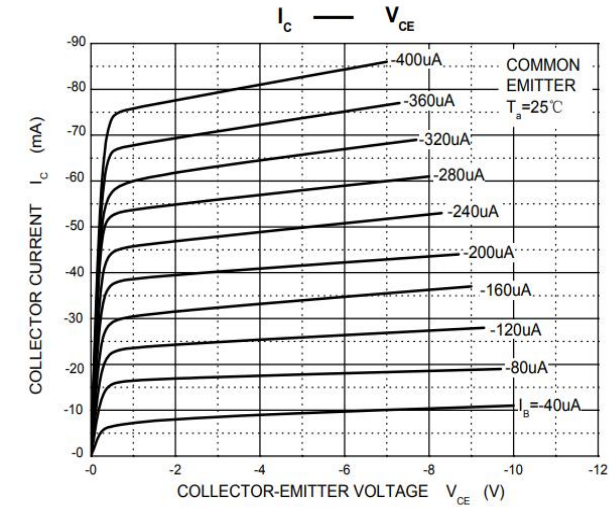
### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter (参数名称)	Symbol (符号)	Test conditions (测试条件)	MIN (最小值)	TYP (典型值)	MAX (最大值)	UNIT (单位)
Collector-base breakdown voltage 集电极-基极击穿电压	V(BR)CBO	IC= -100μA, IE=0	-40			V
Collector-emitter breakdown voltage 集电极-发射极击穿电压	V(BR)CEO	IC= -1mA, IB=0	-25			V
Emitter-base breakdown voltage 发射极-基极击穿电压	V(BR)EBO	IE=-100μA, IC=0	-5			V
Collector cut-off current 集电极-基极截止电流	ICBO	VCB=-30 V, IE=0			-1	μ A
Collector cut-off current 集电极-发射极截止电流	ICEO	VCE=-25V, IB=0			-10	μ A
Emitter cut-off current 发射极-基极截止电流	IEBO	VEB=-5V, IC=0			-1	μ A
DC current gain 直流电流增益	hFE	VCE=-1V, IC= -50mA	80		400	
Collector-emitter saturation voltage 集电极-发射极饱和电压	VCE(sat)	IC=-500mA, IB= -50mA			-0.5	V
Base-emitter saturation voltage 发射极-基极饱和电压	VBE(sat)	IC=-500mA, IB= -50mA			-1.2	V

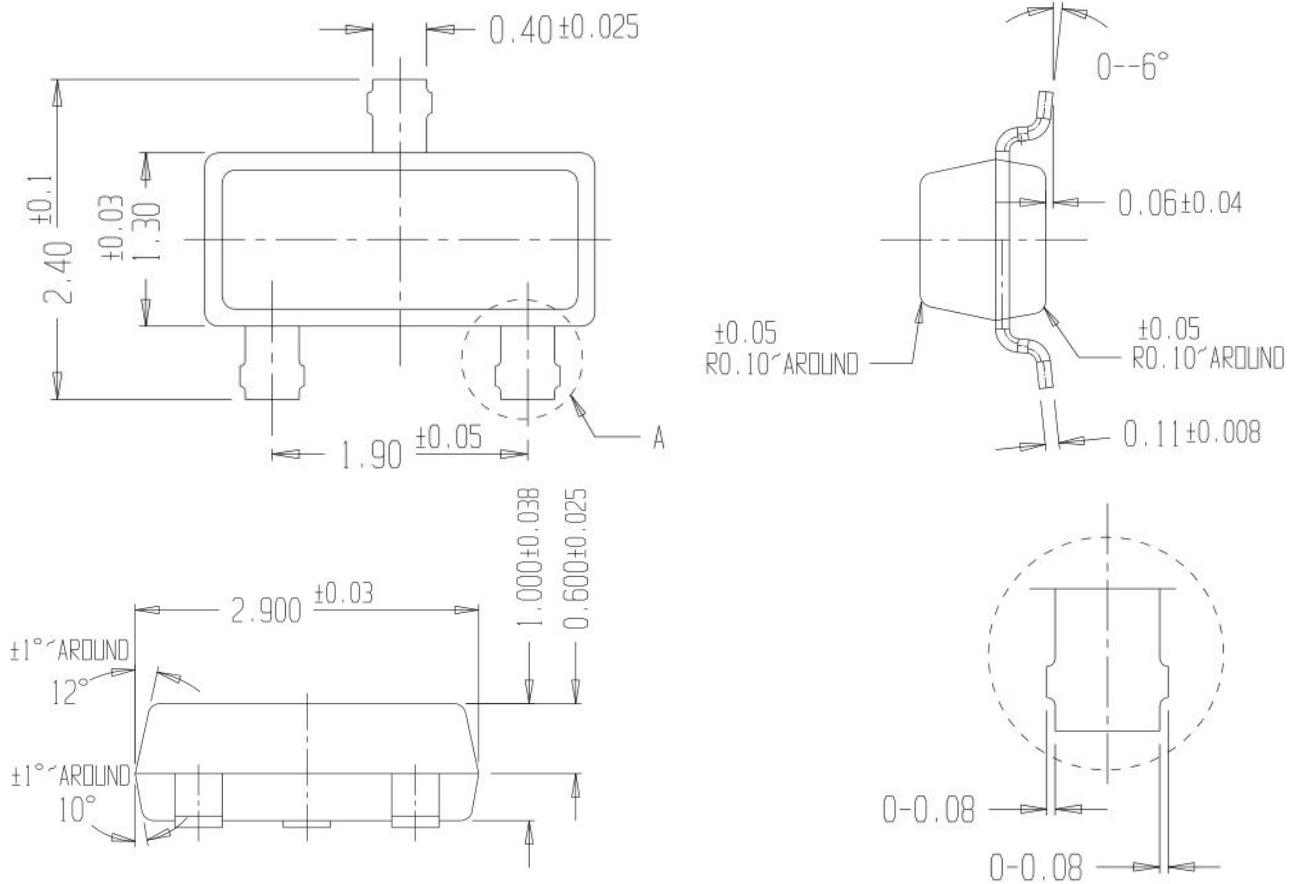
### CLASSIFICATION OF hFE

Range	80-100	100-200	200-400

## Typical Characteristics



### SOT-23 Package information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	0.962	1.038	0.038	0.040
A1	0.575	0.625	0.023	0.025
b	0.40	0.60	0.016	0.024
c	0.08	0.15	0.003	0.06
D	2.87	2.93	0.113	0.115
E	1.27	1.33	0.05	0.052
E1	2.3	2.5	0.090	0.098
e 1	1.85	1.95	0.073	0.077
L	0.31	0.44	0.012	0.017
L1	0.50	0.60	0.020	0.024
e	0.02	0.1	0.000	0.004